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STB85NS04Z STB85NS04Z-1

N-channel 11mΩ - 80A - D²PAK - I²PAK
SAFeFET™ Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STB85NS04Z	Clamped	< 0.015Ω	80A ⁽¹⁾
STB85NS04Z-1	Clamped	< 0.015Ω	80A ⁽¹⁾

1. Current limited by wire bonding

- 100% avalanche tested
- Low capacitance and gate charge
- 175°C maximum junction temperature

Description

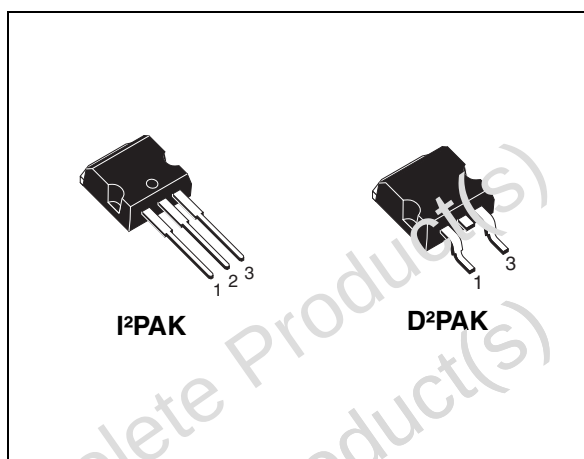
This fully clamped Power MOSFET is produced by using the latest advanced Company's Mesh Overlay™ process which is based on a novel strip layout. The inherent benefits of the new technology coupled with the extra clamping capabilities make this product particularly suitable for the harshest operation conditions such as those encountered in the automotive environment. Any other application requiring extra ruggedness is also recommended.

Applications

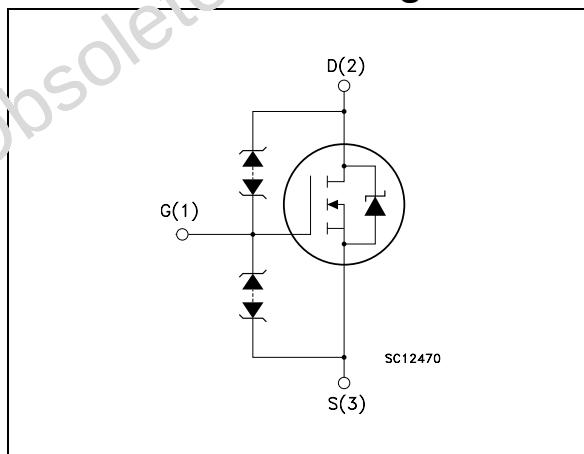
- Switching application
 - Automotive

Order codes

Part number	Marking	Package	Packaging
STB85NS04ZT4	B85NS04Z	D ² PAK	Tape & reel
STB85NS04Z-1	B85NS04Z-1	I ² PAK	Tube



Internal schematic diagram



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STB85NS04Z - STB85NS04Z-1

Electrical ratings

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS}=0$)	33 ⁽¹⁾	V
V_{GS}	Gate-source voltage	± 18	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	80 ⁽²⁾	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	60	A
I_{DG}	Drain gate current (continuous)	± 50	nA
I_{GS}	Gate source current (continuous)	± 50	mA
$I_{DM}^{(3)}$	Drain current (pulsed)	320	A
	Derating factor	1.43	W/°C
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	215	W
$V_{ESD(G-S)}$	Gate-source ESD (HBM-C=100pF, R=1.5k Ω)	2	kV
$V_{ESD(G-D)}$	Gate-drain ESD (HBM-C=100pF, R=1.5k Ω)	4	kV
$V_{ESD(D-S)}$	Drain-source ESD (HBM-C=100pF, R=1.5k Ω)	4	kV
T_j	Operating junction temperature	-55 to 175	°C
T_{stg}	Storage temperature		

1. Voltage is limited by reverse diodes
2. Current limited by wire bonding
3. Pulse width limited by safe operating area

Table 2. Thermal data

Symbol	Parameter	Value		Unit
		D ² PAK	I ² PAK	
$R_{thj-case}$	Thermal resistance junction-case max	0.7		°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	35	--	°C/W
$R_{thj-amb}$	Thermal resistance junction-amb max	62.5		°C/W
T_l	Maximum lead temperature for soldering purpose	300		°C

1. When mounted on 1inch² FR-4 board, 2 oz Cu

Electrical ratings

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Table 3. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max)	60	A
E_{AS}	Single pulse avalanche energy (starting $T_J=25^{\circ}\text{C}$, $I_D=I_{AS}$, $V_{DD}=30\text{V}$)	550	mJ

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Electrical characteristics

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0	33			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = 16V, V _{DS} = 16V, T _c =125°C			10 100	μA μA
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ±10V			10	μA
V _{GSS}	Gate-source breakdown voltage	I _{GS} = 100μA	13		25	V
R _G	Series gate resistance			14		Ω
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 1mA	2	3	4	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10V, I _D = 30A		11	15	mΩ

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g _{fs}	Forward transconductance	V _{DS} = 25V, I _D = 30A		50		S
C _{iss}	Input capacitance	V _{DS} = 25V, f = 1MHz, V _{GS} = 0		2500		pF
C _{oss}	Output capacitance			800		pF
C _{rss}	Reverse transfer capacitance			150		pF
Q _g	Total gate charge	V _{DD} = 16V, I _D = 60A		68	100	nC
Q _{gs}	Gate-source charge	V _{GS} = 10V		15		nC
Q _{gd}	Gate-drain charge	(see Figure 14)		19		nC

Electrical characteristics

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Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage rise time	$V_{clamp}=30V, I_D=60A$		85		ns
t_f	Fall time	$R_G=4.7\Omega, V_{GS}=10V$		145		ns
t_c	Cross-over time	(see Figure 15)		90		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				80	A
I_{SDM}	Source-drain current (pulsed)				320	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD}=60A, V_{GS}=0$			1.5	V
t_{rr}	Reverse recovery time	$I_{SD}=60A, V_{DD}=100V$		65		ns
Q_{rr}	Reverse recovery charge	$di/dt=25A/\mu s, T_j=150^\circ C$		0.15		μC
I_{RRM}	Reverse recovery current	(see Figure 18)		4.5		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

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Electrical characteristics

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

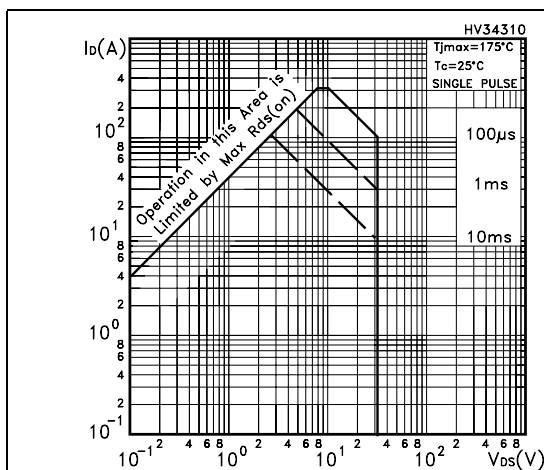


Figure 2. Thermal impedance

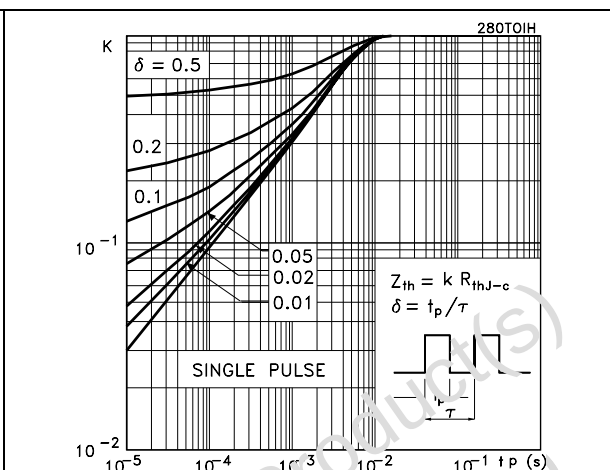


Figure 3. Output characteristics

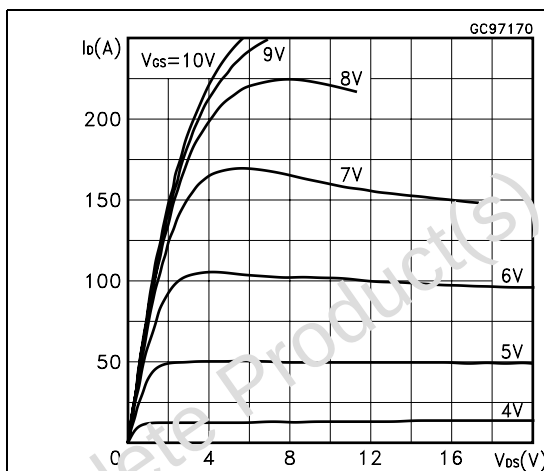


Figure 4. Transfer characteristics

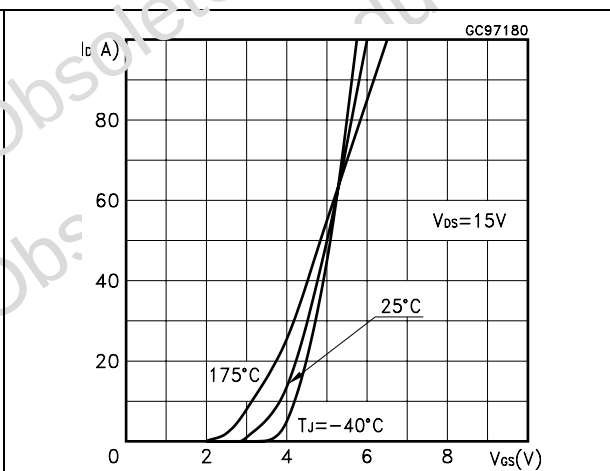


Figure 5. Transconductance

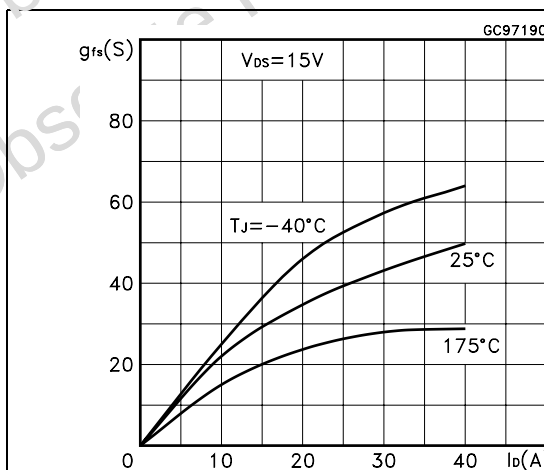
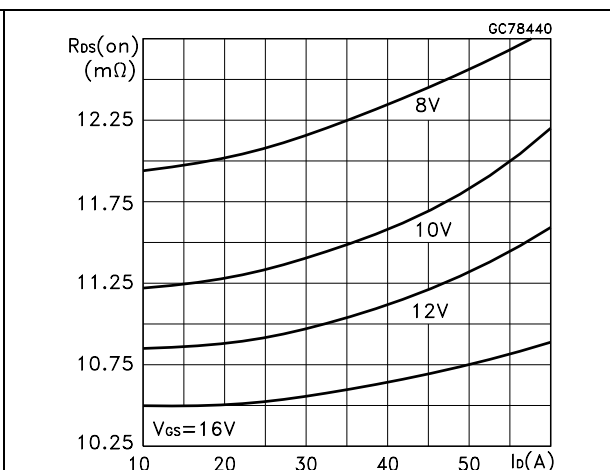


Figure 6. Static drain-source on resistance



Electrical characteristics

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Figure 7. Gate charge vs gate-source voltage **Figure 8. Capacitance variations**

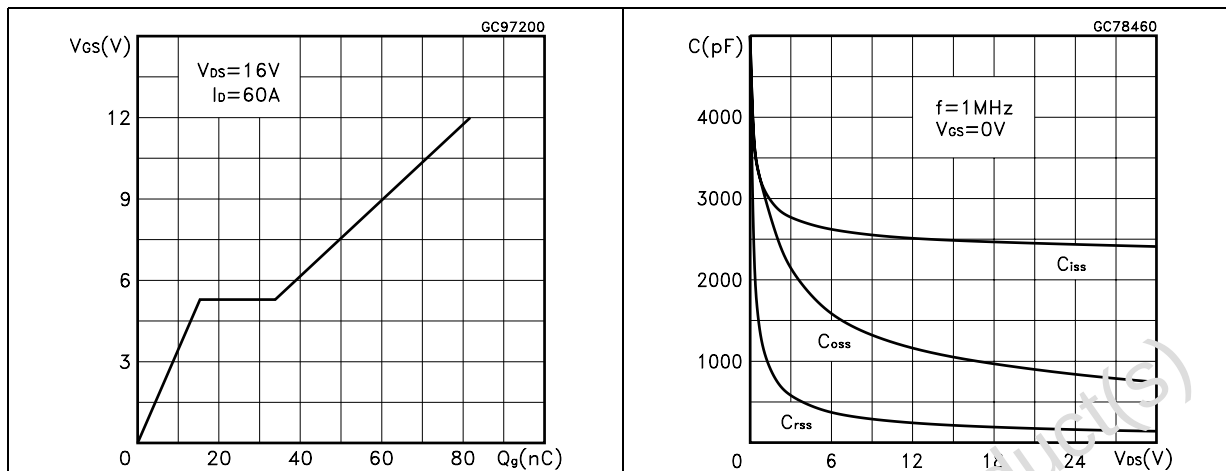


Figure 9. Normalized gate threshold voltage vs temperature **Figure 10. Normalized on resistance vs temperature**

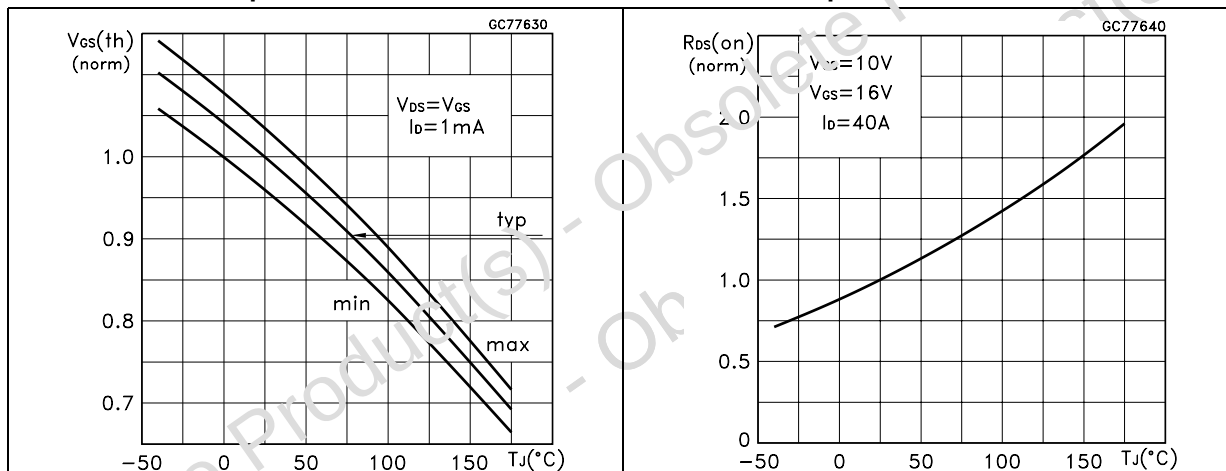
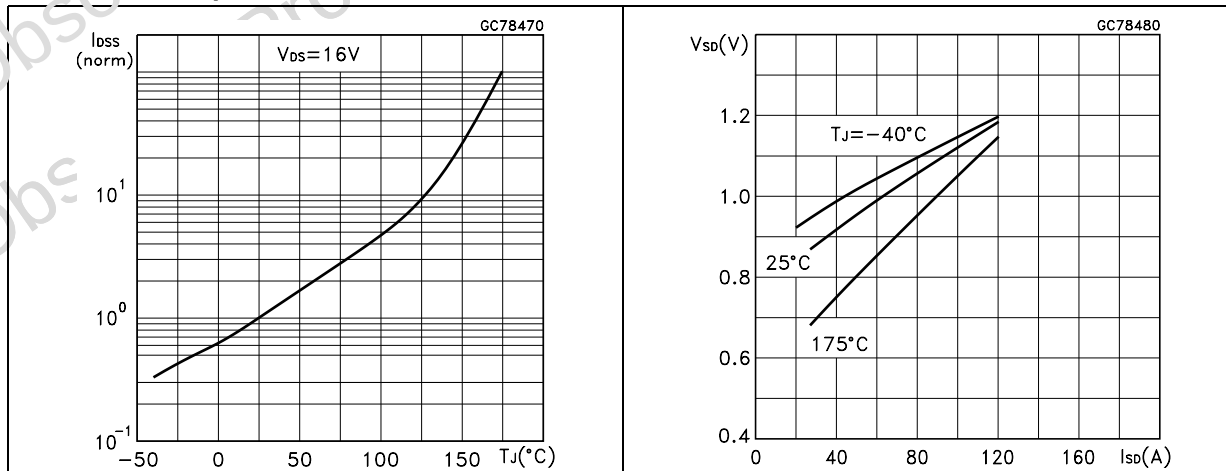


Figure 11. Zero gate voltage drain current vs temperature **Figure 12. Source-drain diode forward characteristics**



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Test circuit

3 Test circuit

Figure 13. Switching times test circuit for resistive load

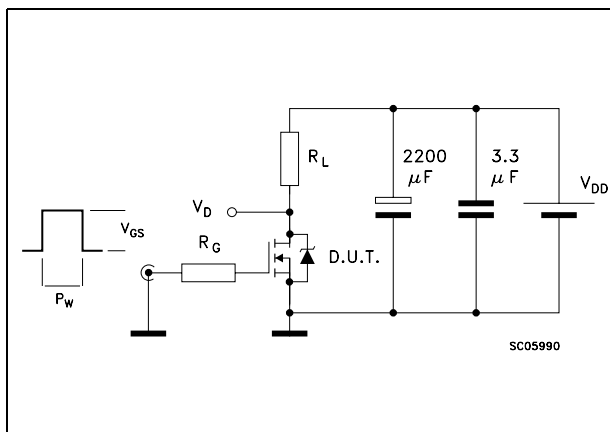


Figure 14. Gate charge test circuit

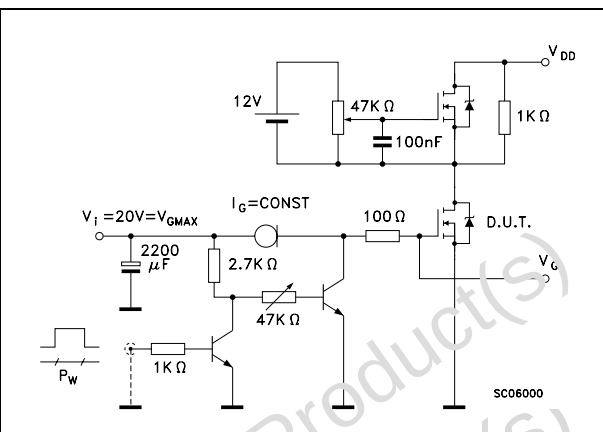


Figure 15. Test circuit for inductive load switching and diode recovery times

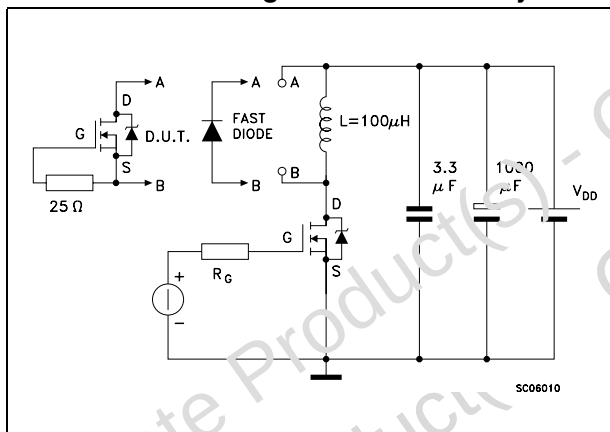


Figure 16. Unclamped inductive load test circuit

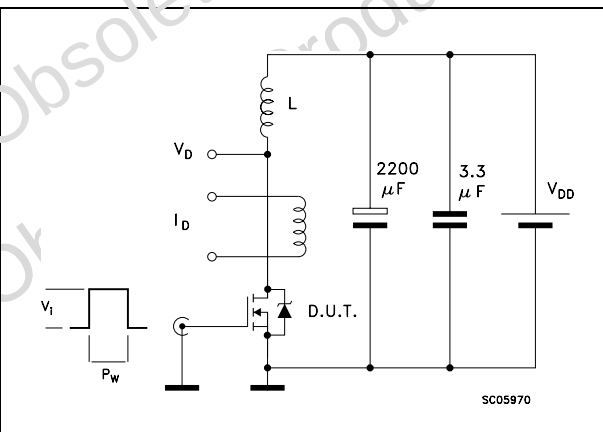


Figure 17. Unclamped inductive waveform

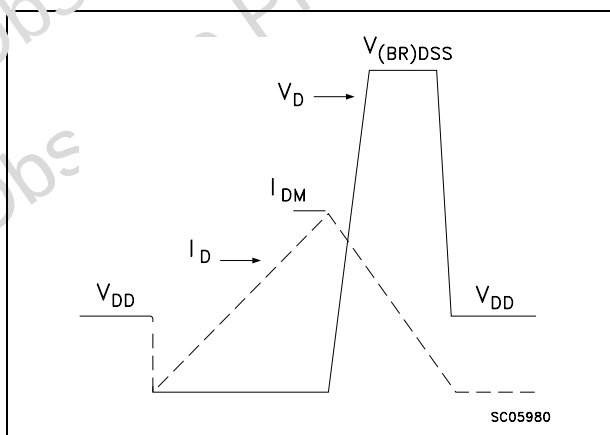
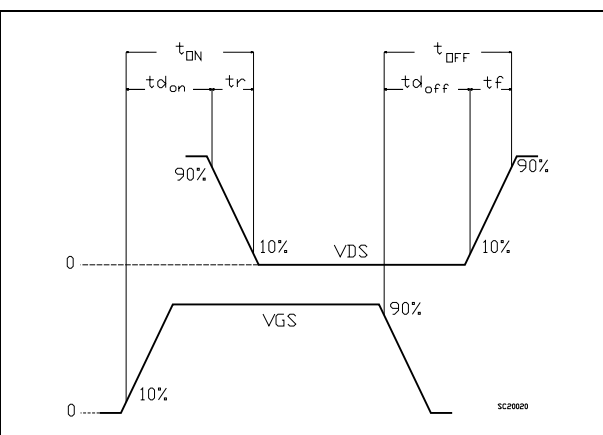


Figure 18. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

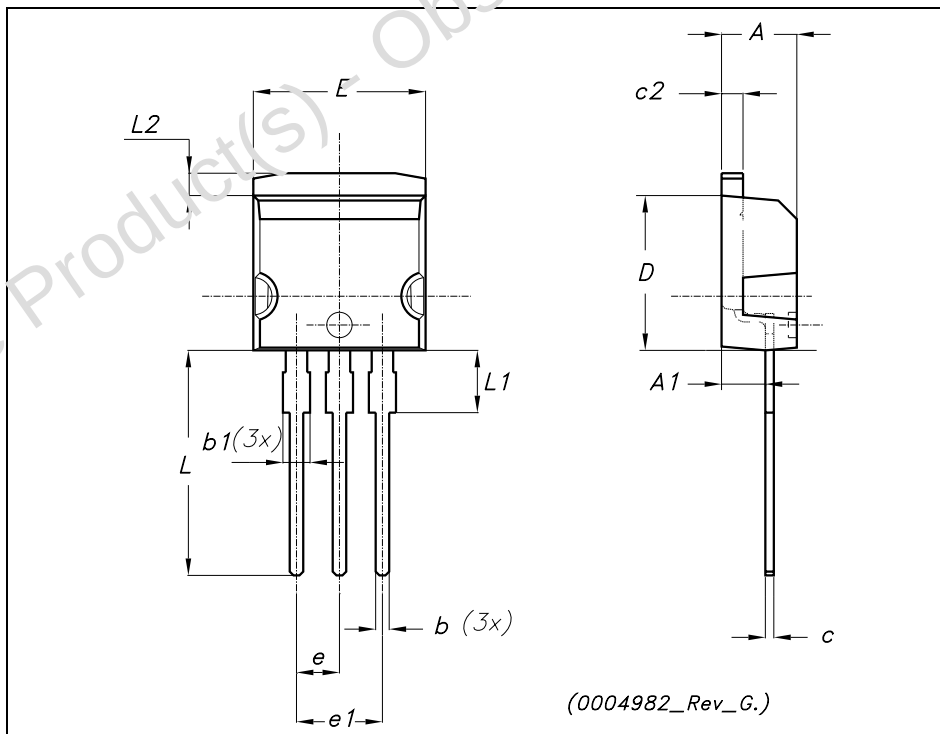
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Package mechanical data

TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055

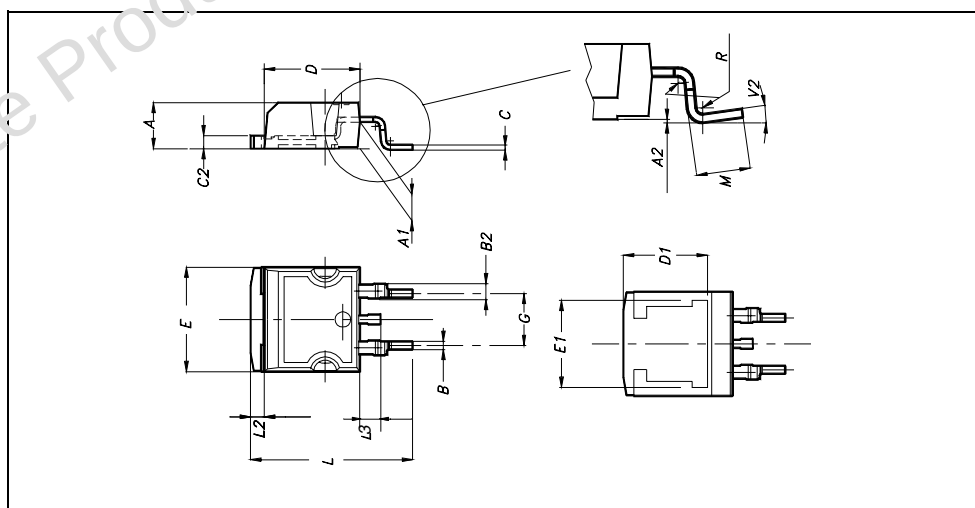


Package mechanical data

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D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

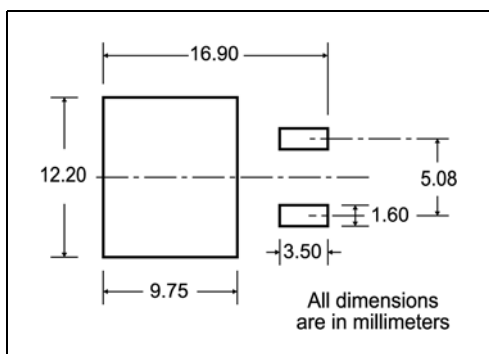


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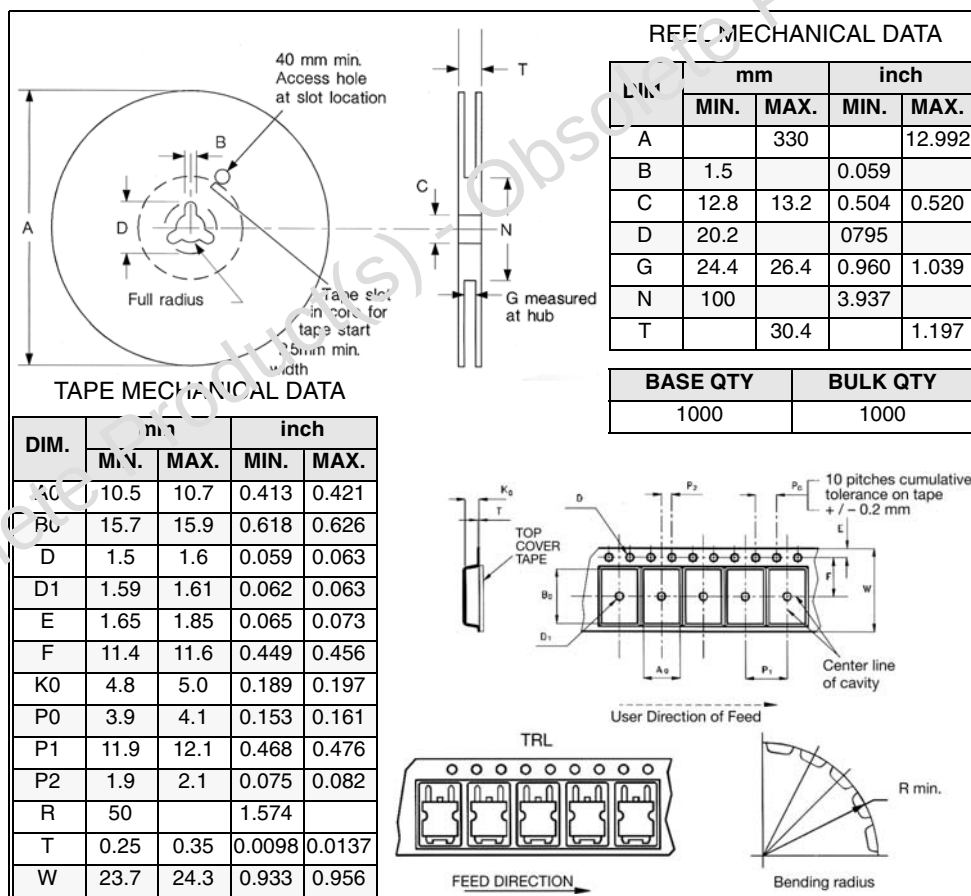
Packaging mechanical data

5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

Revision history

STB85NS04Z - STB85NS04Z-1

6 Revision history

Table 8. Revision history

Date	Revision	Changes
25-Sep-2006	1	First release

STB85NS04Z - STB85NS04Z-1

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